

HE8807SG/FL

GaAlAs Infrared Emitting Diodes

Description

The HE8807SG/FL are single heterojunction structure GaAlAs light emitting diodes with a wavelength of 880 nm.

Features

- High output, high efficiency
- Narrow spectral width
- Sharp radiation directivity (HE8807FL)
- Wide radiation directivity (HE8807SG)
- High reliability

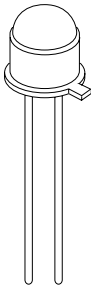
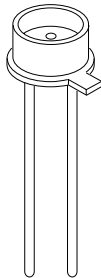
Absolute Maximum Ratings [Tc=25°C]			
Item	Symbol	Value	Unit
Forward Current	IF	200	mA
Reverse Voltage	VR	3	V
Operating Temperature	TOPR	-20 ~ +85	°C
Storage Temperature	TSTG	-40 ~ +100	°C

Electro-Optical Characteristics [Tc=25°C]							
Item		Symbol	Condition	Minimum	Typical	Maximum	Unit
Optical Output Power	HE8807SG	Po	IF=150mA	10			mW
	HE8807FL	Pf*	IF=20mA	0.5			
Peak Wavelength		λP	IF=150mA	800	880	900	nm
Spectral Width		Δλ	IF=150mA		30	60	nm
Forward Voltage		VF	IF=150mA		1.7	2.3	V
Reverse Current		IR	VR=3V			100	μA
Capacitance		Ct	VR=0V, f=1MHz		10		pF
Rise Time		tr	IF=50mA		20		ns
Fall Time		tf	IF=50mA		20		ns

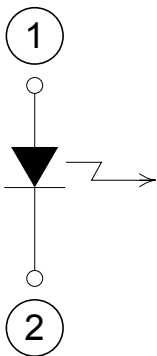
* Pf specification: The optical output within 9 degrees of the acceptance angle.

Package Type

- HE8807SG: SG1
- HE8807FL: FL

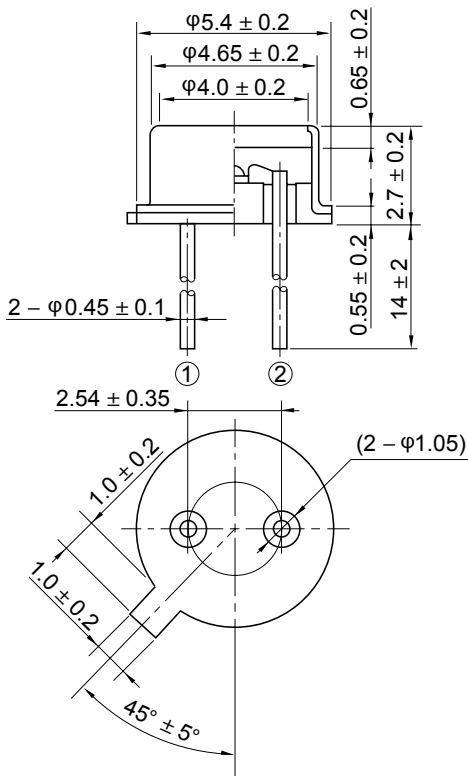


Internal Circuit



Package Dimensions (Unit:mm)

SG1-type



FL-type

